

AMENDMENTS TO THE CLAIMS

Claims 1-8. (Canceled)

9. (Currently Amended) An apparatus ~~for incorporating an impurity in a thin film on a substrate arranged in a deposition chamber~~ comprising:
 a low pressure deposition chamber;
 a substrate arranged within the deposition chamber, the substrate comprising an impurity incorporated in a thin film formed in the deposition chamber; and
 an impurity cell located entirely within [[in]] the deposition chamber and the impurity cell is not coupled to a heat source so as to provide the impurity by desorption due to low pressure in the deposition chamber, the impurity cell comprising:
 a substantially solid material having exposed surfaces located entirely within the deposition chamber; and
 an impurity-containing fluid adhered on said exposed surfaces.
10. (Original) The apparatus of claim 9, wherein the impurity is selected from the group consisting of carbon and germanium.
11. (Original) The apparatus of claim 9, wherein the thin film comprises epitaxial or polycrystalline silicon.
12. (Original) The apparatus of claim 11, wherein the impurity incorporated into the epitaxial or polycrystalline silicon thin film comprises carbon in a concentration from about $1\text{E}13$ atoms/cm³ to a maximum solubility of carbon in the silicon thin film.

Claims 13-15 (Canceled).

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16. (Original) The apparatus of claim 9, wherein the deposition chamber comprises a vacuum chamber.

Claims 17-32. (Canceled)

33. (Previously Presented) The apparatus of claim 9, wherein the impurity-containing fluid comprises a liquid or a gas.
34. (Previously Presented) The apparatus of claim 33, wherein the gas comprises methane, ethane, propane or butane.
35. (Currently Amended) The apparatus of claim 33, wherein the liquid comprises a liquid alkane selected from pentane, hexane, heptane, octane, or nonane, ~~or the like~~.
36. (Previously Presented) The apparatus of claim 9, wherein a layer of the impurity-containing fluid is adhered on said exposed surfaces.
37. (Previously Presented) The apparatus of claim 9, wherein the substantially solid material comprises porous, curvaceous or pitted features.
38. (Previously Presented) The apparatus of claim 9, wherein the substantially solid material comprises metal, ceramic, Teflon, stainless steel, alumina, silica or zirconia.
39. (Previously Presented) The apparatus of claim 9 further comprising:
an enclosure in the deposition chamber, the impurity cell located in the enclosure;
and
an impurity source coupled to the enclosure.

40. (Previously Presented) The apparatus of claim 39, wherein the enclosure and the impurity source are coupled by a connector.
41. (Previously Presented) The apparatus of claim 40, wherein the connector includes a valve, wherein when the valve is in one state the enclosure and the impurity source are isolated, and when the valve is in another state the impurity cell can be charged by the impurity source.
42. (Previously Presented) The apparatus of claim 39, wherein the impurity source is external to the deposition chamber.